TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K01F

High Speed Switching Applications

Unit: mm

- Small package
- Low on resistance: Ron = 120 m Ω (max) (VGS = 4 V)

: Ron = 150 m Ω (max) (VGS = 2.5 V)

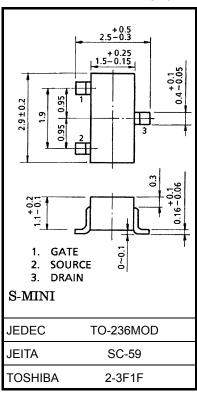
• Low gate threshold voltage: $V_{th} = 0.6 \sim 1.1 \text{ V (VDS} = 3 \text{ V, ID} = 0.1 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DS}	30	V	
Gate-source voltage		V _{GSS}	±10	V	
Drain current	DC	ID	1.3	Α	
	Pulse	I _{DP}	2.6		
Drain power dissipation		P _D	200	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Note:

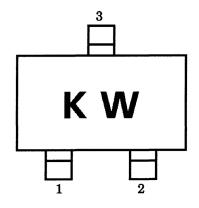
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



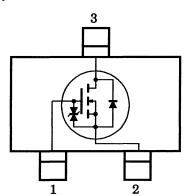
Weight: 0.012 g (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking



Equivalent Circuit



Handling Precaution

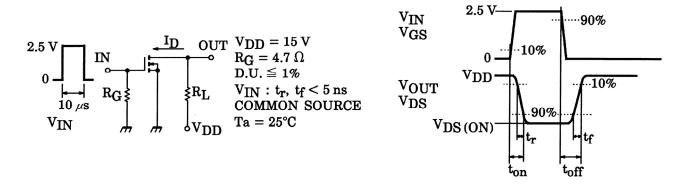
When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	_	_	±5	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	30	_	_	V
Drain cut-off curre	ent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0	_	_	1	μА
Gate threshold vo	oltage	V _{th}	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.6	_	1.1	V
Forward transfer	admittance	Y _{fs}	V _{DS} = 3 V, I _D = 0.65 A (Note	2.0	_	_	S
Drain-source ON resistance		R _{DS (ON)}	I _D = 0.65 A, V _{GS} = 4 V (Note	e) —	85	120	mΩ
			I _D = 0.65 A, V _{GS} = 2.5 V (Note	:) —	115	150	
Input capacitance	capacitance C_{iss} $V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		_	152	_	pF	
Reverse transfer	capacitance	C _{rss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		41	_	pF
Output capacitance		Coss	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	102	_	pF
Switching time	Turn-on time	t _{on}	$V_{DD} = 15 \text{ V}, I_D = 0.5 \text{ A}, V_{GS} = 0~2.5 \text{ V}, R_G = 4.7 \Omega$, —	45	_	- ns
	Turn-off time	t _{off}		_	69	_	

Note: Pulse test

Switching Time Test Circuit

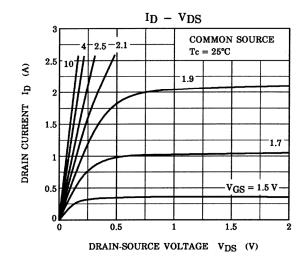


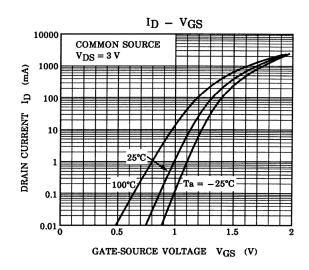
Precaution

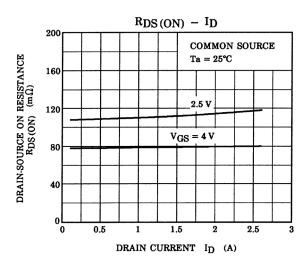
 V_{th} can be expressed as voltage between gate and source when low operating current value is ID = 100 μ A for this product. For normal switching operation, VGS (ON) requires higher voltage than V_{th} and VGS (off) requires lower voltage than V_{th} .

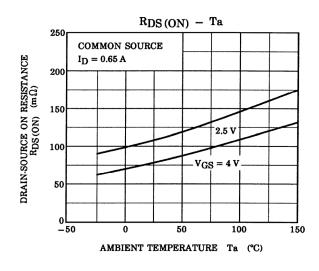
(Relationship can be established as follows: V_{GS} (off) $< V_{th} < V_{GS}$ (ON))

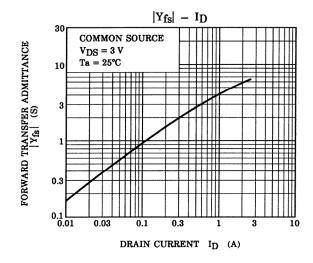
Please take this into consideration for using the device.

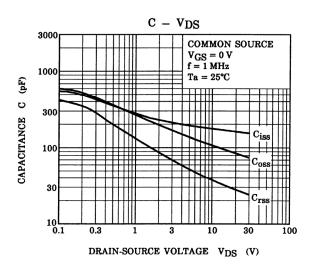




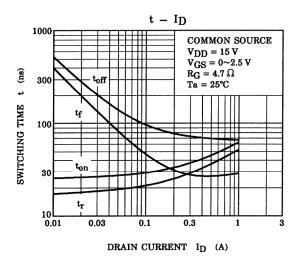


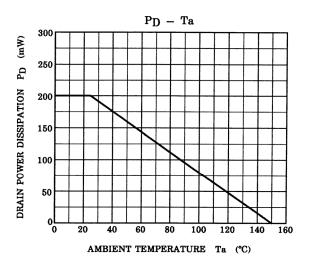






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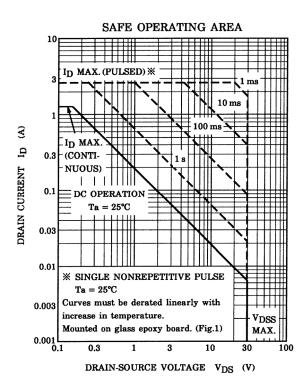




Figure 1 25.4 mm \times 25.4 mm \times 1.6 t (a Cu pad of 0.8 mm² area)

RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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